



## SOT-23 Plastic-Encapsulate Transistors

### MMBTA06 TRANSISTOR (NPN)

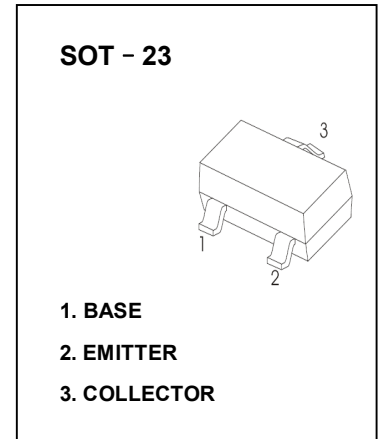
#### FEATURES

- For Switching and Amplifier Applications
- Complementary Type PNP Transistor MMBTA56

#### MARKING: 1GM

#### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	80	V
$V_{CEO}$	Collector-Emitter Voltage	80	V
$V_{EBO}$	Emitter-Base Voltage	4	V
$I_C$	Collector Current	500	mA
$P_C$	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	416	$^{\circ}\text{C/W}$
$T_j$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^{\circ}\text{C}$



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#### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}, I_C=0$	4			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=80\text{V}, I_E=0$			0.1	$\mu\text{A}$
Collector cut-off current	$I_{CES}$	$V_{CE}=60\text{V}, I_B=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=3\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$	100		400	
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			1.2	V
Transition frequency	$f_T$	$V_{CE}=2\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100			MHz

# Typical Characteristics

# MMBTA06

